Complementary Silicon Plastic Power Transistors

Designed for use in general purpose amplifier and switching applications.

Features

- High Current Gain Bandwidth Product
- Compact TO-220 Package
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit			
Collector – Emitter Voltage TIP31G, TIP32G TIP31AG, TIP32AG TIP31BG, TIP32BG TIP31CG, TIP32CG	V _{CEO}	40 60 80 100	Vdc			
Collector–Base Voltage TIP31G, TIP32G TIP31AG, TIP32AG TIP31BG, TIP32BG TIP31CG, TIP32CG	V _{CB}	40 60 80 100	Vdc			
Emitter-Base Voltage	V _{EB}	5.0	Vdc			
Collector Current – Continuous	Ι _C	3.0	Adc			
Collector Current – Peak	I _{CM}	5.0	Adc			
Base Current	I _B	1.0	Adc			
Total Power Dissipation @ T _C = 25°C Derate above 25°C	PD	40 0.32	W W/∘C			
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	2.0 0.016	W W/∘C			
Unclamped Inductive Load Energy (Note 1)	E	32	mJ			
Operating and Storage Junction Tem- perature Range	T _J , T _{stg}	-65 to +150	°C			

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. $I_C = 1.8 \text{ A}, L = 20 \text{ mH}, P.R.F. = 10 \text{ Hz}, V_{CC} = 10 \text{ V}, R_{BE} = 100 \Omega$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	R_{\thetaJA}	62.5	°C/W
Thermal Resistance, Junction-to-Case	$R_{ ext{ heta}JC}$	3.125	°C/W

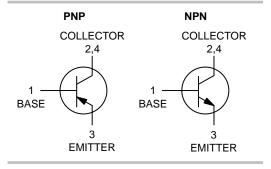
*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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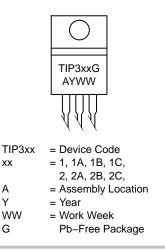
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3 AMPERE POWER TRANSISTORS COMPLEMENTARY SILICON 40–60–80–100 VOLTS, 40 WATTS





MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

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Symbol	Min	Max	Unit
I			•
V _{CEO(sus)}	40 60 80 100	- - - -	Vdc
ICEO	-	0.3 0.3	mAdc
ICES	- - -	200 200 200 200	μAdc
I _{EBO}	_	1.0	mAdc
h _{FE}	25 10	_ 50	-
V _{CE(sat)}	-	1.2	Vdc
V _{BE(on)}	-	1.8	Vdc
f _T	3.0	_	MHz
h _{fe}	20	-	_
	ICEO ICES ICES ICES IEBO VEE(sat) VBE(on)	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c c c c c c c c c c c c c c c c c c c $

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.

TIP31G, TIP31AG, TIP31BG, TIP31CG (NPN), TIP32G, TIP32AG, TIP32BG, TIP32CG (PNP)

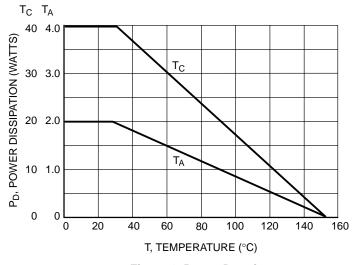
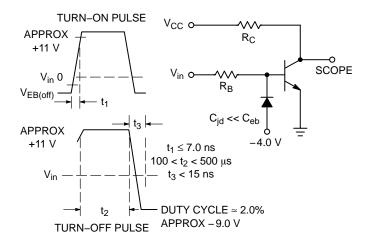
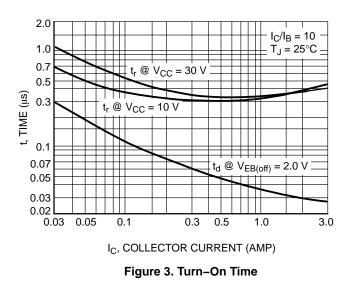


Figure 1. Power Derating



 R_B and R_C VARIED TO OBTAIN DESIRED CURRENT LEVELS.





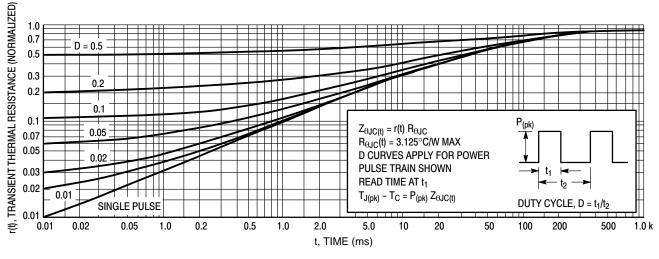


Figure 4. Thermal Response

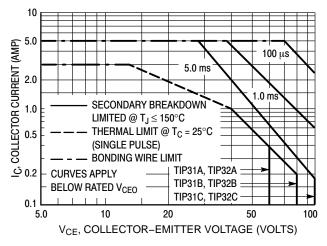
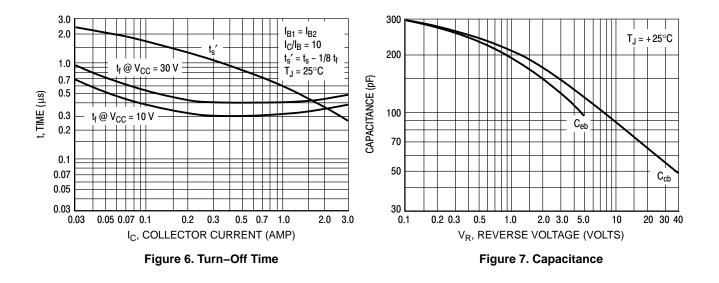
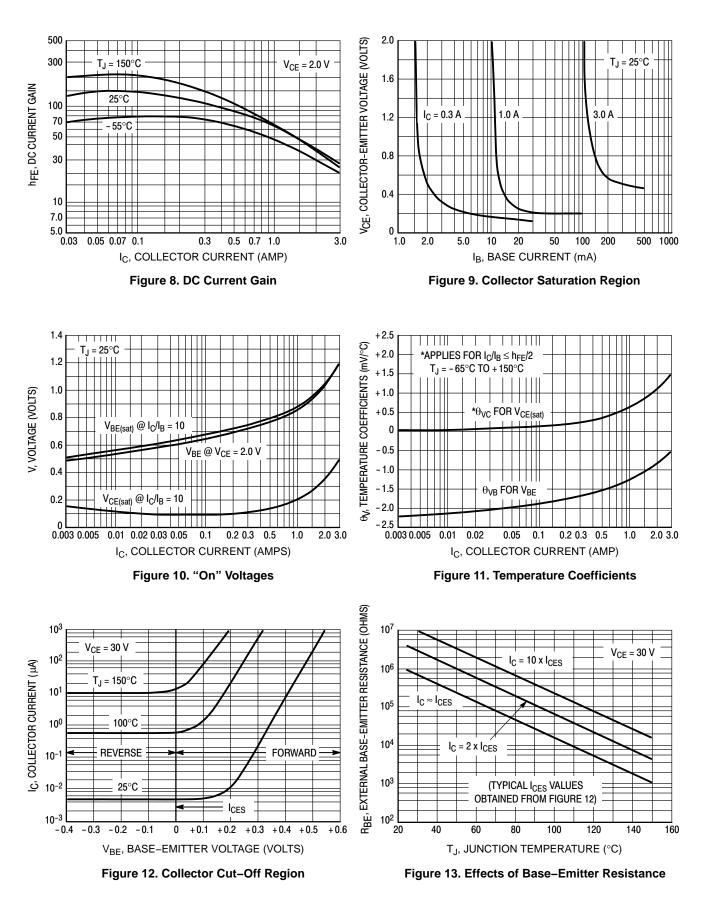


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.





ORDERING INFORMATION

Device	Package	Shipping				
TIP31G	TO-220 (Pb-Free)	50 Units / Rail				
TIP31AG	TO-220 (Pb-Free)	50 Units / Rail				
TIP31BG	TO-220 (Pb-Free)	50 Units / Rail				
TIP31CG	TO-220 (Pb-Free)	50 Units / Rail				
TIP32G	TO-220 (Pb-Free)	50 Units / Rail				
TIP32AG	TO-220 (Pb-Free)	50 Units / Rail				
TIP32BG	TO-220 (Pb-Free)	50 Units / Rail				
TIP32CG	TO-220 (Pb-Free)	50 Units / Rail				

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				4. MAX V	WIDTH FOR	F102 DEVICE	= 1.3510101		
	I	Γ I			INC	HES	MILLIM	ETERS	
				DIM	MIN.	MAX.	MIN.	MAX.	
	2 3			А	0.570	0.620	14.48	15.75	
<u> </u>	┟┰┟┟╌┙──┼			В	0.380	0.415	9.66	10.53	
⊢	₩+₩++			С	0.160	0.190	4.07	4.83	
	í lí	f I		D	0.025	0.038	0.64	0.96	
' z –	I I K			F	0.142	0.161	3.60	4.09	
	î î			G	0.095	0.105	2.42	2.66	
				н	0.110	0.161	2.80	4.10	
	¥ ₩	й I		J	0.014	0.024	0.36	0.61	
V —	R —			ĸ	0.500	0.562	12.70 1.15	14.27	
G	J-	╼║╼		N	0.045	0.060	4.83	1.52 5.33	
Ŭ,	' → → D			Q	0.190	0.210	2.54	3.04	
_	N -			R	0.100	0.120	2.54	2.79	
				s	0.030	0.055	1.15	1.41	
				т	0.235	0.255	5.97	6.47	
				U U	0.000	0.050	0.00	1.27	
				v	0.045		1.15		
				z		0.080		2.04	
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